

# SWITCHMODE™

## NPN Bipolar Power Transistor For Switching Power Supply Applications

The MJE18002 have an applications specific state-of-the-art die designed for use in 220 V line operated Switchmode Power supplies and electronic light ballasts. These high voltage/high speed transistors offer the following:

- Improved Efficiency Due to Low Base Drive Requirements:
  - High and Flat DC Current Gain  $h_{FE}$
  - Fast Switching
  - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot-to-Lot
- Standard TO-220

### MAXIMUM RATINGS

Rating	Symbol	MJE18002	Unit
Collector-Emitter Sustaining Voltage	$V_{CEO}$	450	Vdc
Collector-Emitter Breakdown Voltage	$V_{CES}$	1000	Vdc
Emitter-Base Voltage	$V_{EBO}$	9.0	Vdc
Collector Current – Continuous	$I_C$	2.0	Adc
– Peak(1)	$I_{CM}$	5.0	
Base Current – Continuous	$I_B$	1.0	Adc
– Peak(1)	$I_{BM}$	2.0	
Total Device Dissipation Derate above 25°C	$P_D$	50 0.4	Watts W/°C
Operating and Storage Temperature	$T_J, T_{stg}$	-65 to 150	°C

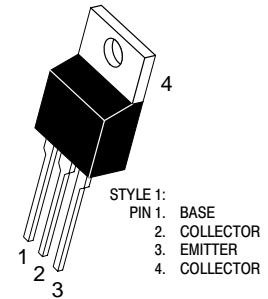
### THERMAL CHARACTERISTICS

Rating	Symbol	MJE18002	Unit
Thermal Resistance – Junction to Case	$R_{\theta JC}$	2.5	°C/W
– Junction to Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	$T_L$	260	°C

## MJE18002\*

\*ON Semiconductor Preferred Device

**POWER TRANSISTOR**  
**2.0 AMPERES**  
**1000 VOLTS**  
**50 WATTS**



**CASE 221A-09**  
**TO-220AB**  
**MJE18002**

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MJE18002

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Sustaining Voltage ( $I_C = 100\text{ mA}$ , $L = 25\text{ mH}$ )	$V_{CEO(sus)}$	450	–	–	Vdc
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CEO}$ , $I_B = 0$ )	$I_{CEO}$	–	–	100	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CES}$ , $V_{EB} = 0$ ) ( $V_{CE} = 800\text{ V}$ , $V_{EB} = 0$ )	$I_{CES}$	–	–	100	$\mu\text{Adc}$
		–	–	500	
		–	–	100	
Emitter Cutoff Current ( $V_{EB} = 9.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	–	100	$\mu\text{Adc}$

## ON CHARACTERISTICS

Base–Emitter Saturation Voltage ( $I_C = 0.4\text{ Adc}$ , $I_B = 40\text{ mAdc}$ ) ( $I_C = 1.0\text{ Adc}$ , $I_B = 0.2\text{ Adc}$ )	$V_{BE(sat)}$	–	0.825	1.1	Vdc
		–	0.92	1.25	
Collector–Emitter Saturation Voltage ( $I_C = 0.4\text{ Adc}$ , $I_B = 40\text{ mAdc}$ )  @ $T_C = 125^\circ\text{C}$	$V_{CE(sat)}$	–	0.2	0.5	Vdc
		–	0.2	0.5	
( $I_C = 1.0\text{ Adc}$ , $I_B = 0.2\text{ Adc}$ )  @ $T_C = 125^\circ\text{C}$		–	0.25	0.5	
		–	0.3	0.6	
DC Current Gain ( $I_C = 0.2\text{ Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ )  @ $T_C = 125^\circ\text{C}$	$h_{FE}$	14	–	34	–
		–	27	–	
( $I_C = 0.4\text{ Adc}$ , $V_{CE} = 1.0\text{ Vdc}$ )  @ $T_C = 125^\circ\text{C}$		11	17	–	
		11	20	–	
( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 1.0\text{ Vdc}$ )  @ $T_C = 125^\circ\text{C}$		6.0	8.0	–	
		5.0	8.0	–	
( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )  @ $T_C = 125^\circ\text{C}$		10	20	–	

## DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ( $I_C = 0.2\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$f_T$	–	13	–	MHz		
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	–	35	60	pF		
Input Capacitance ( $V_{EB} = 8.0\text{ V}$ )	$C_{ib}$	–	400	600	pF		
Dynamic Saturation:  determined 1.0 $\mu\text{s}$ and 3.0 $\mu\text{s}$ after rising $I_{B1}$ reach 0.9 final $I_{B1}$ (see Figure 18)	$V_{CE(dsat)}$				Vdc		
$I_C = 0.4\text{ A}$ $I_{B1} = 40\text{ mA}$ $V_{CC} = 300\text{ V}$		1.0 $\mu\text{s}$	@ $T_C = 125^\circ\text{C}$	–	3.5	–	
		3.0 $\mu\text{s}$	@ $T_C = 125^\circ\text{C}$	–	8.0	–	
				–	1.5	–	
				–	3.8	–	
$I_C = 1.0\text{ A}$ $I_{B1} = 0.2\text{ A}$ $V_{CC} = 300\text{ V}$		1.0 $\mu\text{s}$	@ $T_C = 125^\circ\text{C}$	–	8.0	–	
		3.0 $\mu\text{s}$	@ $T_C = 125^\circ\text{C}$	–	14	–	
				–	2.0	–	
				–	7.0	–	

(1) Pulse Test: Pulse Width = 5.0 ms, Duty Cycle  $\leq 10\%$ .

(2) Proper strike and creepage distance must be provided.

# MJE18002

## ELECTRICAL CHARACTERISTICS – continued ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS: Resistive Load ( $D.C. \leq 10\%$ , Pulse Width = 20 $\mu\text{s}$ )

Turn-On Time	$I_C = 0.4 \text{ Adc}$ $I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc}$ $V_{CC} = 300 \text{ V}$	@ $T_C = 125^\circ\text{C}$	$t_{on}$	–	200	300	ns
Turn-Off Time		@ $T_C = 125^\circ\text{C}$	$t_{off}$	–	1.2	2.5	$\mu\text{s}$
Turn-On Time	$I_C = 1.0 \text{ Adc}$ $I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc}$ $V_{CC} = 300 \text{ V}$	@ $T_C = 125^\circ\text{C}$	$t_{on}$	–	85	150	ns
Turn-Off Time		@ $T_C = 125^\circ\text{C}$	$t_{off}$	–	1.7	2.5	$\mu\text{s}$

### SWITCHING CHARACTERISTICS: Inductive Load ( $V_{clamp} = 300 \text{ V}$ , $V_{CC} = 15 \text{ V}$ , $L = 200 \mu\text{H}$ )

Fall Time	$I_C = 0.4 \text{ Adc}$ , $I_{B1} = 40 \text{ mAdc}$ , $I_{B2} = 0.2 \text{ Adc}$	@ $T_C = 125^\circ\text{C}$	$t_{fi}$	–	125	200	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	$t_{si}$	–	0.7	1.25	$\mu\text{s}$
Crossover Time		@ $T_C = 125^\circ\text{C}$	$t_c$	–	110	200	ns
Fall Time	$I_C = 1.0 \text{ Adc}$ , $I_{B1} = 0.2 \text{ Adc}$ , $I_{B2} = 0.5 \text{ Adc}$	@ $T_C = 125^\circ\text{C}$	$t_{fi}$	–	110	175	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	$t_{si}$	–	1.7	2.75	$\mu\text{s}$
Crossover Time		@ $T_C = 125^\circ\text{C}$	$t_c$	–	200	300	ns
Fall Time	$I_C = 0.4 \text{ Adc}$ , $I_{B1} = 50 \text{ mAdc}$ , $I_{B2} = 50 \text{ mAdc}$	@ $T_C = 125^\circ\text{C}$	$t_{fi}$	–	140	200	ns
Storage Time		@ $T_C = 125^\circ\text{C}$	$t_{si}$	–	2.2	3.0	$\mu\text{s}$
Crossover Time		@ $T_C = 125^\circ\text{C}$	$t_c$	–	140	250	ns

TYPICAL STATIC CHARACTERISTICS

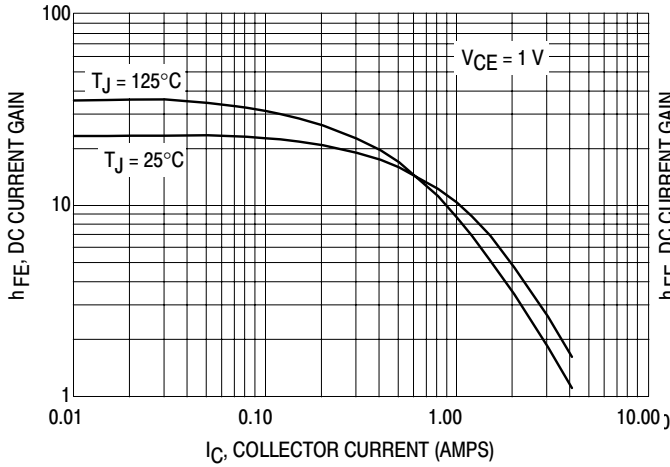


Figure 1. DC Current Gain @ 1 Volt

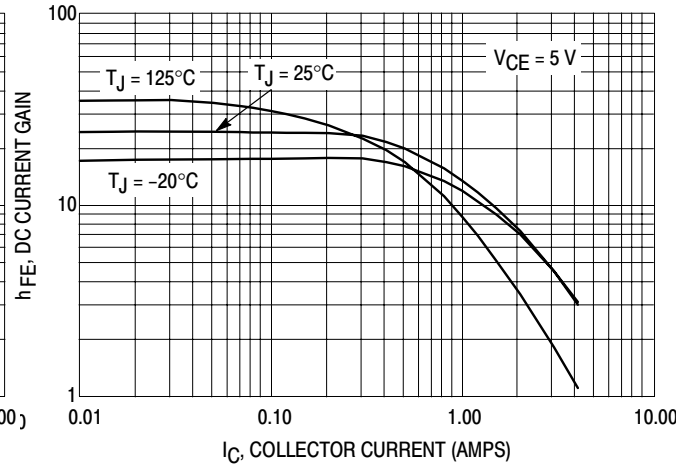


Figure 2. DC Current Gain @ 5 Volts

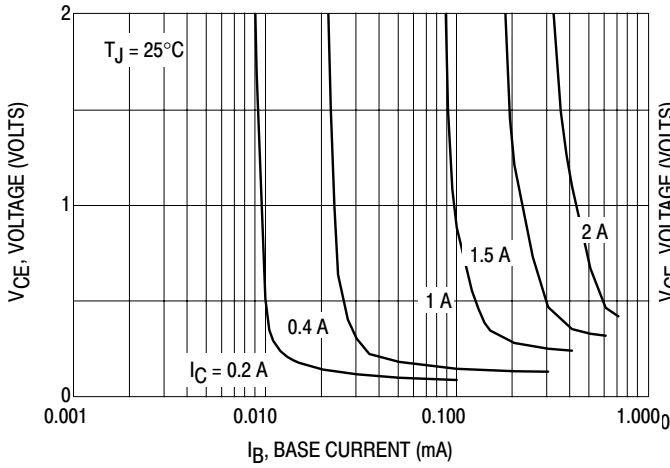


Figure 3. Collector Saturation Region

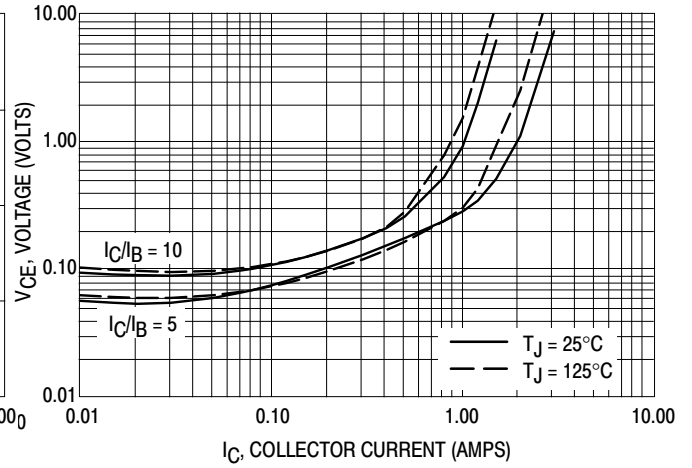


Figure 4. Collector-Emitter Saturation Voltage

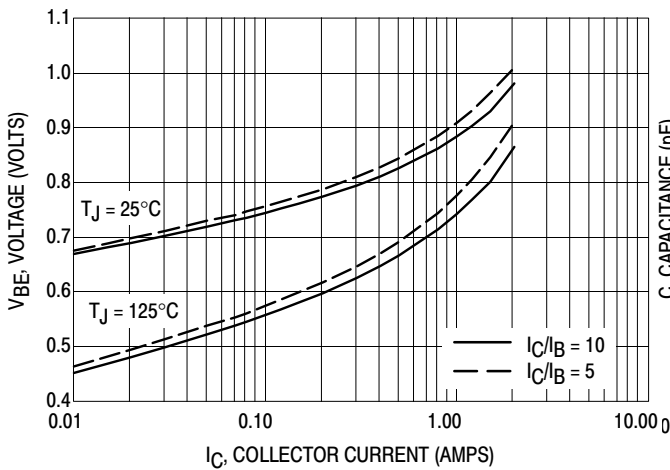


Figure 5. Base-Emitter Saturation Region

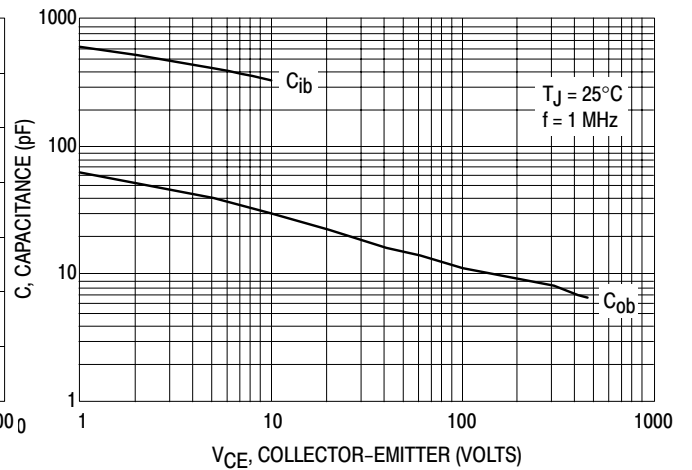


Figure 6. Capacitance

TYPICAL SWITCHING CHARACTERISTICS  
( $I_{B2} = I_C/2$  for all switching)

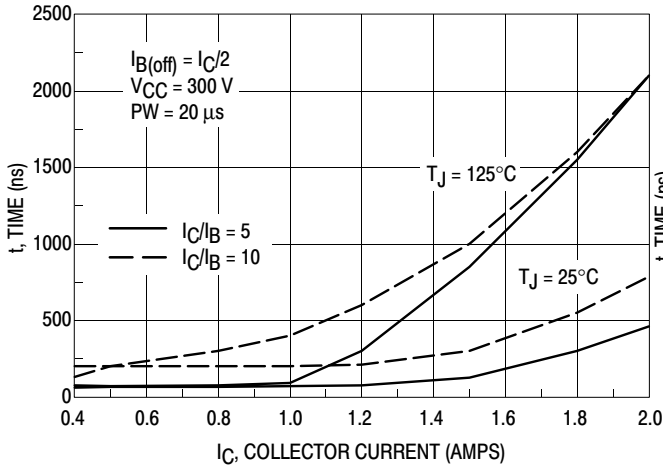


Figure 7. Resistive Switching,  $t_{on}$

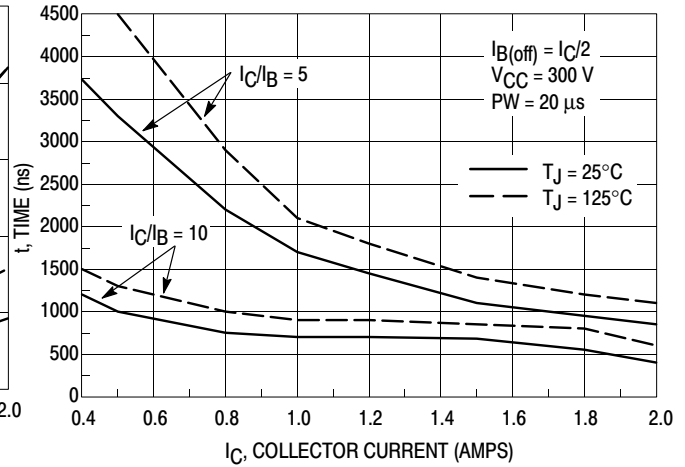


Figure 8. Resistive Switching,  $t_{off}$

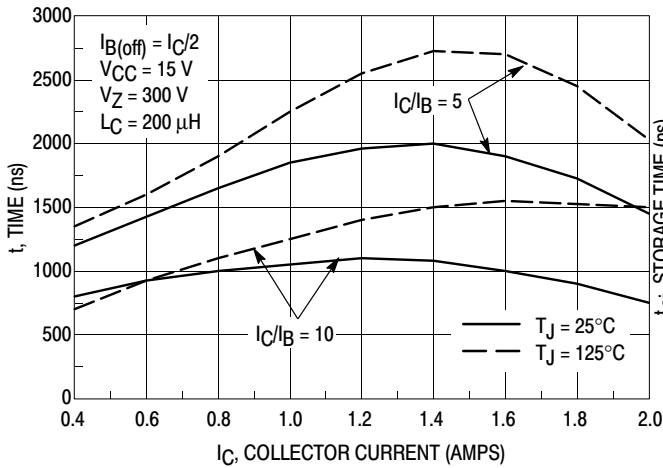


Figure 9. Inductive Storage Time,  $t_{si}$

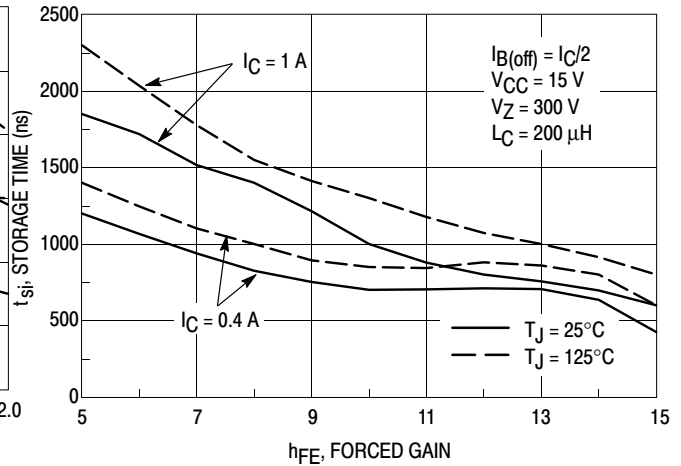


Figure 10. Inductive Storage Time

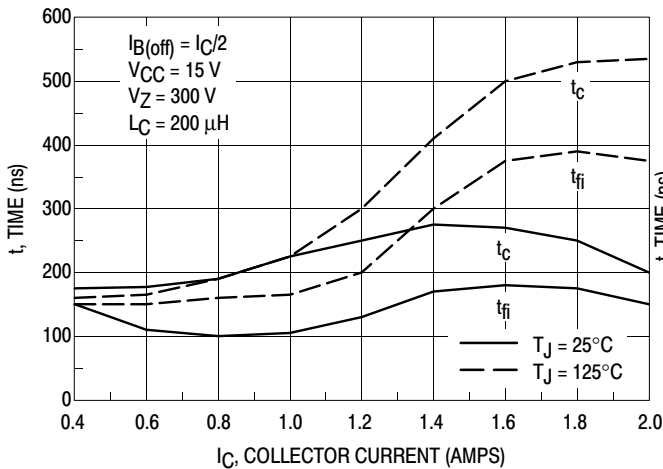


Figure 11. Inductive Switching,  $t_c$  and  $t_{fi}$ ,  $I_C/I_B = 5$

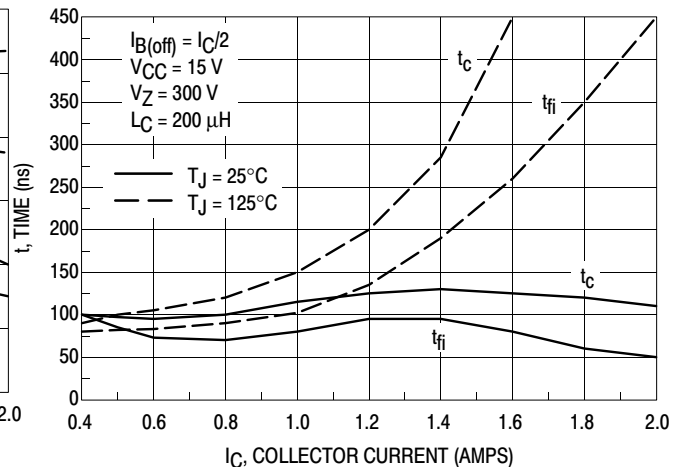


Figure 12. Inductive Switching,  $t_c$  and  $t_{fi}$ ,  $I_C/I_B = 10$

**TYPICAL SWITCHING CHARACTERISTICS**  
( $I_{B2} = I_C/2$  for all switching)

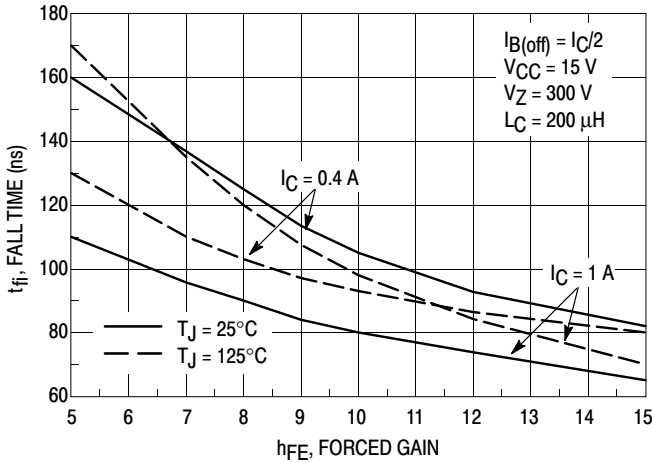


Figure 13. Inductive Fall Time

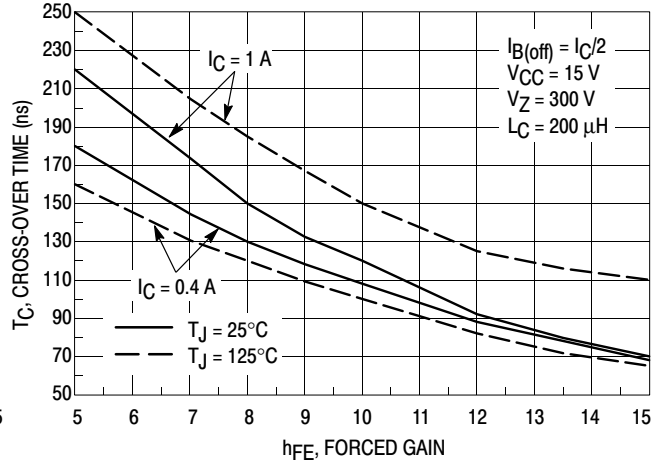


Figure 14. Inductive Crossover Time

**GUARANTEED SAFE OPERATING AREA INFORMATION**

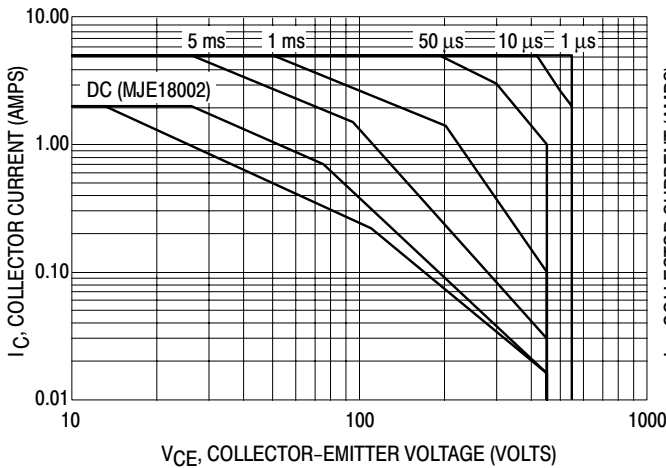


Figure 15. Forward Bias Safe Operating Area

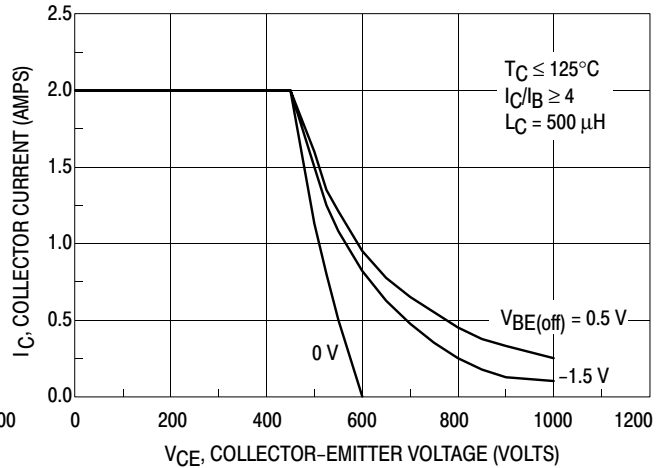


Figure 16. Reverse Bias Switching Safe Operating Area

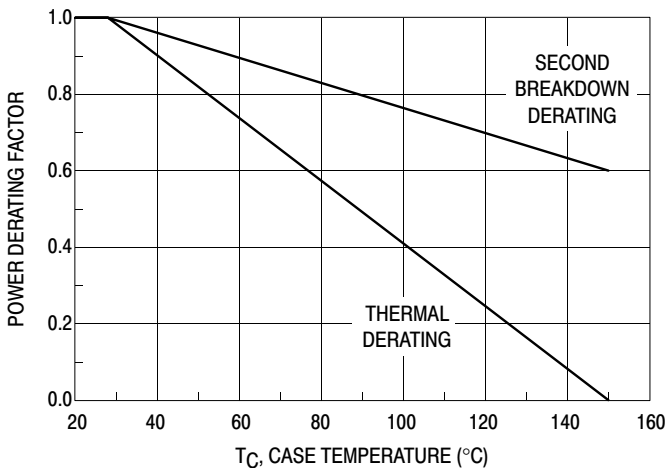


Figure 17. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on  $T_C = 25^\circ\text{C}$ ;  $T_J(\text{pk})$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when  $T_C > 25^\circ\text{C}$ . Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17.  $T_J(\text{pk})$  may be calculated from the data in Figures 20 and NO TAG. At any case temperatures, thermal limitations will reduce the power that can be handled to values less the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base to emitter junction reverse biased. The safe level is specified as a reverse biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

# MJE18002

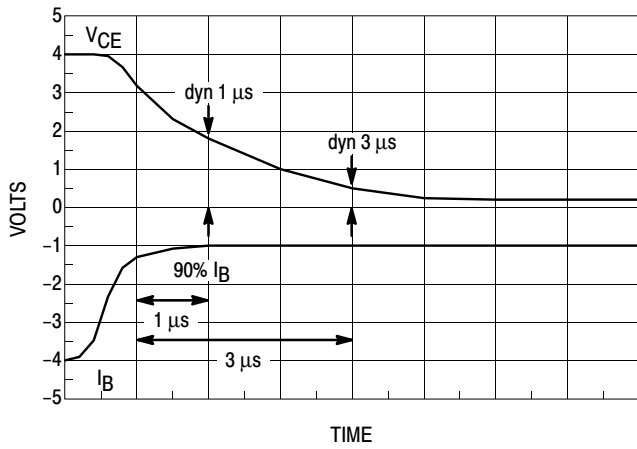


Figure 18. Dynamic Saturation Voltage Measurements

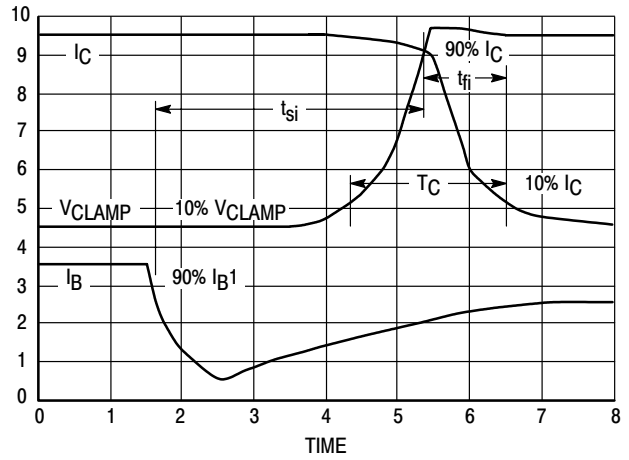
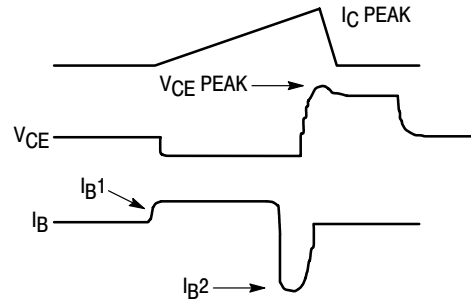
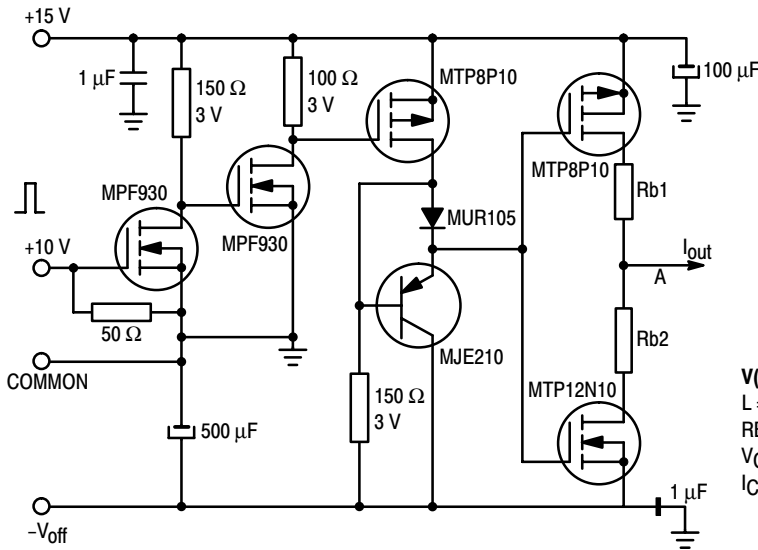


Figure 19. Inductive Switching Measurements



V(BR)CEO(sus)	INDUCTIVE SWITCHING	RBSOA
L = 10 μH	L = 200 μH	L = 500 μH
RB2 = ∞	RB2 = 0	RB2 = 0
VCC = 20 VOLTS	VCC = 15 VOLTS	VCC = 15 VOLTS
IC(pk) = 100 mA	RB1 SELECTED FOR DESIRED IB1	RB1 SELECTED FOR DESIRED IB1

Table 1. Inductive Load Switching Drive Circuit

## TYPICAL THERMAL RESPONSE

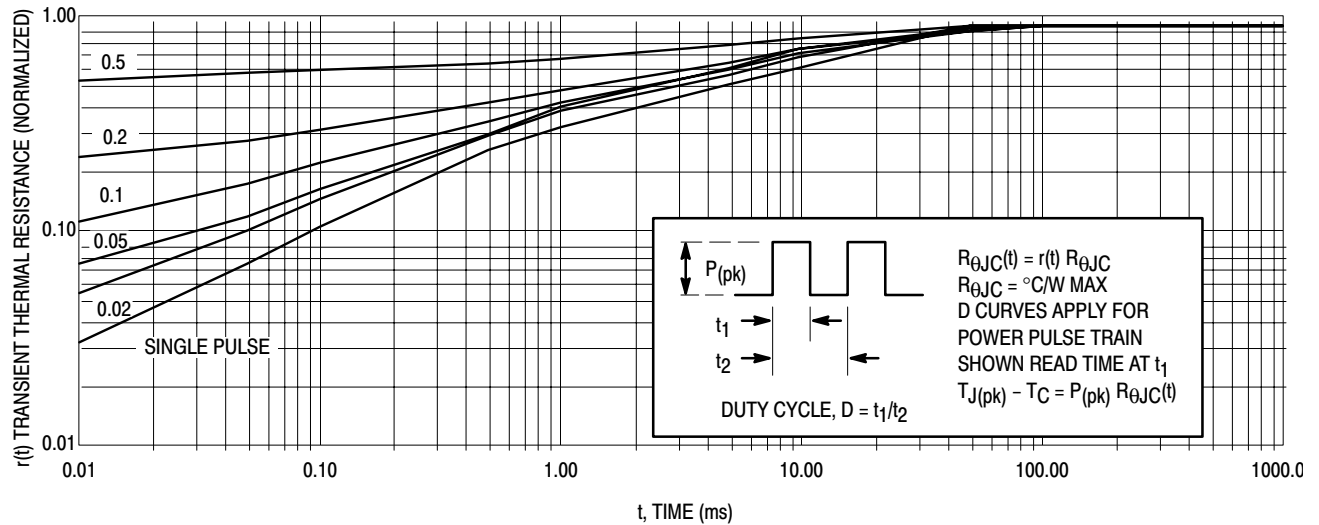
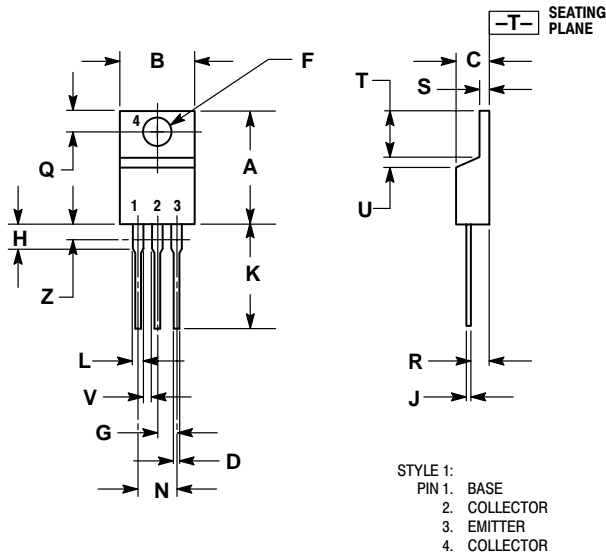


Figure 20. Typical Thermal Response ( $Z_{\theta JC}(t)$ ) for MJE18002

# MJE18002

## PACKAGE DIMENSIONS

### TO-220AB CASE 221A-09 ISSUE AA




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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